



#### 20V NPN HIGH GAIN POWER TRANSISTOR IN SOT23F

#### **Features**

- BV<sub>CEO</sub> > 20V
- BV<sub>CEX</sub> > 65V
- BV<sub>ECO</sub> > 4.5V
- I<sub>C</sub> = 7A Continuous Collector Current
- Very Low V<sub>CE(SAT)</sub> < 30mV @ 1A</li>
- R<sub>CE(SAT)</sub> = 18mΩ
- 1.5W Power Dissipation
- High Forward Blocking Voltage
- High Gain
- Complementary PNP Type: ZXTP19020CFF
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Description**

Advanced process capability has been used to maximize the performance of this transistor. The SOT23F package is compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

## **Mechanical Data**

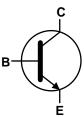
- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>®</sup>
- Weight: 0.012 grams (Approximate)

#### **Applications**

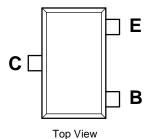
- MOSFET and IGBT Gate Driving
- LED Driving
- Strobe Flash
- Motor Drive
- Micro Buffers



Top View



Device Symbol



Pin Configuration

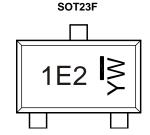
#### **Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTN19020CFFTA	AEC-Q101	1E2	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



1E2 = Product Type Marking Code YW = Date Code Marking

 $\underline{Y} = \text{Year} : 0 \sim 9$ 

 $\overline{W}$  = Week : A~Z : 1~26 a~z : 27~52

z represents 52 & 53 week

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# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	65	V
Collector-Emitter Voltage (Forward Blocking)	V <sub>CEX</sub>	65	V
Collector-Emitter Voltage (Base Open)	V <sub>CEO</sub>	20	V
Emitter-Collector Voltage (Reverse Blocking)	V <sub>ECO</sub>	4.5	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	7	A
Peak Pulse Current	Ісм	15	А
Base Current	I <sub>B</sub>	1	А

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.84 6.72		
Power Dissipation	(Note 6)		1.34 10.72	W	
Linear Derating Factor	(Note 7)	P <sub>D</sub>	1.50 12.0	mW/°C	
	(Note 8)		2.0 16.0	1	
	(Note 5)		149		
Thermal Desistance, Investigate Ambient	(Note 6)		93	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	83		
	(Note 8)		60		
Thermal Resistance, Junction to Lead (Note 9)		$R_{ heta JL}$	43.8	°C/W	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

# ESD Ratings (Note 10)

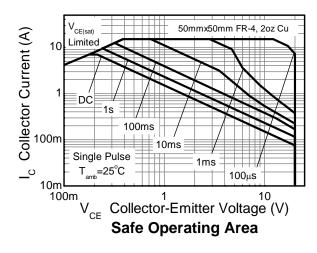
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

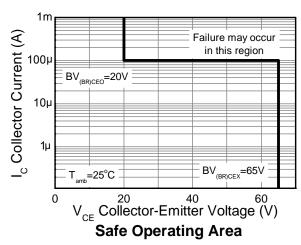
Notes: 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

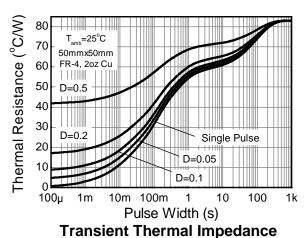
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
- 8. Same as Note 7, whilst measured at t < 5 seconds.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

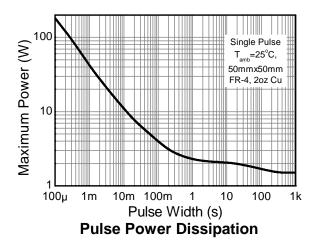


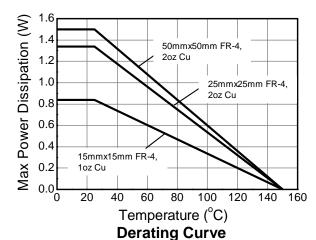
# **Thermal Characteristics and Derating Information**











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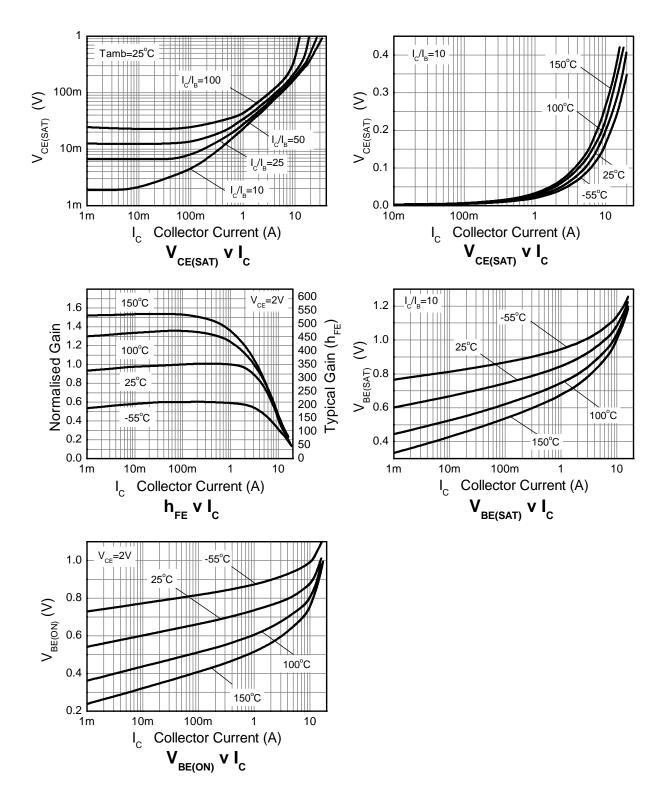
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS	-					
Collector-Base Breakdown Voltage	$BV_{CBO}$	65	85	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Forward Blocking	BV <sub>CEX</sub>	65	85	_	V	$I_C = 100\mu A, R_{BE} < 1k\Omega,$ or -1V < V <sub>BE</sub> < 0.25V
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV <sub>CEO</sub>	20	25	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7	8.3	_	V	$I_{E} = 100 \mu A$
Emitter – Collector Breakdown Voltage (Reverse Blocking)	BV <sub>ECX</sub>	6	8.2	_	V	$I_E = 100\mu A$ , $R_{BC} < 1k\Omega$ , or $V_{BC} = \pm 0.25V$
Emitter – Collector Breakdown Voltage (Base Open)	BV <sub>ECO</sub>	4.5	5.3	_	V	I <sub>E</sub> = 100μA
Collector-Base Cut-off Current	I <sub>CBO</sub>	_	<1 —	50 20	nΑ μΑ	V <sub>CB</sub> = 50V V <sub>CB</sub> = 50V, T <sub>A</sub> = +100°C
Collector-Base Cut-off Current	I <sub>CEX</sub>	_	<1	100	nA	$V_{CE} = 50V, R_{BE} < 1k\Omega \text{ or}$ -1V < $V_{BE} < 0.25V$
Emitter-Base Cut-off Current	I <sub>EBO</sub>	_	<1	50	nA	V <sub>EB</sub> = 5.6V
ON CHARACTERISTICS (Note 11)		•	•	•	•	•
Static Forward Current Transfer Ratio	h <sub>FE</sub>	200 180 100 45	350 340 220 95	500 — — —	_	$I_{C} = 0.1A, V_{CE} = 2V$ $I_{C} = 2A, V_{CE} = 2V$ $I_{C} = 7A, V_{CE} = 2V$ $I_{C} = 15A, V_{CE} = 2V$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	23 45 55 135	30 65 70 175	mV	$I_C = 1A$ , $I_B = 100mA$ $I_C = 1A$ , $I_B = 10mA$ $I_C = 2A$ , $I_B = 40mA$ $I_C = 7A$ , $I_B = 280mA$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	960	1050	mV	$I_C = 7A$ , $I_B = 280mA$
Base-Emitter On Voltage	$V_{BE(ON)}$	_	840	950	mV	$I_C = 7A$ , $V_{CE} = 2V$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	_	150	_	MHz	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V},$ f = 50MHz
Input Capacitance	C <sub>IBO</sub>	_	315		pF	$V_{EB} = 0.5V$ , $f = 1MHz$
Output Capacitance	C <sub>OBO</sub>	_	40	50	pF	V <sub>CB</sub> = 10V, f = 1MHz
Delay Time	t <sub>D</sub>	_	135	_	ns	10)/
Rise Time	t <sub>R</sub>	_	117	_	ns	$V_{CC} = 10V$
Storage Time	ime t <sub>S</sub> -		285	_	ns	$I_{C} = 1A,$ $I_{B1} = -I_{B2} = 10\text{mA}$
Fall Time	t <sub>F</sub>	_	88	_	ns	7 IB1 = - IB2 = TUITA

11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%. Note:



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

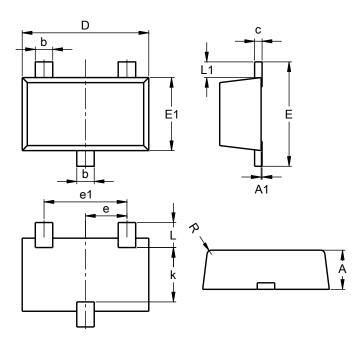




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23F

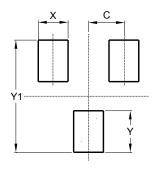


SOT23F						
Dim	Min	Max	Тур			
Α	0.80	1.00	0.90			
A1	0.00	0.10	0.01			
b	0.35	0.50	0.44			
С	0.10	0.20	0.16			
D	2.80	3.00	2.90			
е	0.95 REF					
e1		1.90 RE	F			
Е	2.30	2.50	2.40			
E1	1.50	1.70	1.65			
k	1.20					
L	0.30	0.65	0.50			
L1	0.30	0.50	0.40			
R	0.05	0.15	-			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23F



Dimensions	Value		
Dimensions	(in mm)		
С	0.95		
Х	0.80		
Y	1.110		
Y1	3.000		



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